









	<h2 style="color: red;">FQB12N60TM_AM002</h2>	
	<b>Hersteller-Teilenummer:</b>	<a href="#">FQB12N60TM_AM002</a>
	<b>Hersteller / Marke:</b>	<a href="#">AMI Semiconductor / ON Semiconductor</a>
	<b>Teil der Beschreibung:</b>	MOSFET N-CH 600V 10.5A D2PAK
<b>Datenblätter:</b>	 <a href="#">FQB12N60TM_AM002.pdf</a>	
<b>RoHs Status:</b>	Bleifrei / RoHS-konform	
<b>Lagerzustand:</b>	New original, 32363 pcs Stock Available.	
<b>Liefern von:</b>	Hong Kong	
<b>Versandweg:</b>	DHL/Fedex/TNT/UPS/EMS	
<p>Image may be representation. See specs for product details.</p>		

### Spezifikationen

Teilenummer	<a href="#">FQB12N60TM_AM002</a>
Hersteller	<a href="#">AMI Semiconductor / ON Semiconductor</a>
Beschreibung	MOSFET N-CH 600V 10.5A D2PAK
Kategorie	<a href="#">Diskrete Halbleiterprodukte &gt; Transistoren-FETs,</a>
Teilstatus	32363 pcs Stock
detaillierte Beschreibung	N-Channel 600V 10.5A (Tc) 3.13W (Ta), 180W (Tc)
Serie	QFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-263-3, D <sup>2</sup> Pak (2 Leads + Tab), TO-263AB
Supplier Device-Gehäuse	D <sup>2</sup> PAK (TO-263AB)
Verlustleistung (max)	3.13W (Ta), 180W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	600V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	10.5A (Tc)
Rds On (Max) @ Id, Vgs	700 mOhm @ 5.3A, 10V
VGS (th) (Max) @ Id	5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	54nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	1900pF @ 25V
Antriebsspannung (Max Rds On, Min Rds On)	10V
Vgs (Max)	±30V
Verpackung	Tape & Reel (TR)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)

FQB12N60TM\_AM002 ist neu im Original, Suche FQB12N60TM\_AM002 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie FQB12N60TM\_AM002 AMI Semiconductor / ON Semiconductor mit Garantie und Vertrauen. Anfrage FQB12N60TM\_AM002: [Info@Y-IC.com](mailto:Info@Y-IC.com)

Sie können auch interessiert sein:

 <p><b>FQB12N60</b> FAIRCHI FQB12N60 FAIRCHI</p>	 <p><b>FQB12N60C</b> Fairchild/ON Semiconductor FQB12N60C FAIRCHILD</p>	 <p><b>FQB12P10TM</b> AMI Semiconductor / ON Semiconductor MOSFET P-CH 100V 11.5A D2PAK</p>	 <p><b>FQB12N60TM</b> Fairchild/ON Semiconductor FQB12N60TM FAIRCHILD</p>
 <p><b>FQB12P10TM</b> Fairchild/ON Semiconductor MOSFET P-CH 100V 11.5A D2PAK</p>	 <p><b>FQB12N60CTM</b> AMI Semiconductor / ON Semiconductor MOSFET N-CH 600V 12A D2PAK</p>	 <p><b>FQB12N60CTM</b> Fairchild/ON Semiconductor MOSFET N-CH 600V 12A D2PAK</p>	 <p><b>FQB12P10</b> FSC FQB12P10 FSC</p>

### heiße Teile

Mehr

FQB10N20TM	FQB10N50CF	FQB10N50CFTM	FQB10N50CFTM_WS	FQB10N60C
FQB10N60CTM	FQB10N60CTM	FQB11N40	FQB11N40C	FQB11N40CTM
FQB11N40CTM	FQB11N60FTM	FQB11N60TM	FQB11P06	FQB11P06TM
FQB11P06TM	FQB11P06TM**CN-SCI	FQB12N50TM	FQB12N50TM_AM002	FQB12N50TM_AM002
FQB12N60	FQB12N60C	FQB12N60CTM	FQB12N60CTM	FQB12N60TM
FQB12N60TM_AM002	FQB12P10	FQB12P10TM	FQB12P10TM	FQB12P20
FQB12P20TM	FQB12P20TM	FQB13N06L	FQB13N10	FQB13N10L
FQB13N50	FQB13N50CTM	FQB13N50CTM	FQB140N03L	FQB14N30TM
FQB14N30TM	FQB16N25TM	FQB16N25TM	FQB17P06	FQB17P10
FQB17P10TM	FQB17P10TM	FQB19N10L	FQB19N10LTM	FQB19N10LTM

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